IN THE SPECIFICATION:

Please replace paragraph [0043] with the following amended paragraph:

[0043] While Figures 3A-3F show only one gate device on a substrate, it is recognized that the layers described herein will typically be formed on a substrate that includes a plurality of devices of different sizes, types, and materials and spaced at varying densities across the surface of the substrate. It is believed that the layers promote uniform heating across a surface of the substrate during annealing of the substrate in spite of varying device topography across the surface of a substrate. In particular, it is ~~believe~~ believed that the layers have high emissivities for electromagnetic radiation having a wavelength of between about 808 nm and about 810 nm that promote uniform heating across a surface of the substrate during a laser annealing process in which the substrate is exposed to electromagnetic radiation having a wavelength of between about 808 nm and about 810 nm.

Please replace paragraph [0048] with the following amended paragraph:

[0048] A layer comprising amorphous carbon and nitrogen was deposited on 8 silicon substrates in a PECVD chamber under the following processing conditions: 400°C, 7 Torr, 1200 watts RF power at a frequency of 13.56 MHz, 350 sccm C_3H_6, 3400 sccm N_2, and a spacing of 270 mils between the chamber showerhead and the substrate support. The layer was deposited was deposited in the absence of a chamber shadow ring in Examples 10-15. The layer was deposited with a chamber shadow ring present in Examples 16 and 17. The substrate was then laser annealed according to embodiments provided herein. The thickness of the deposited layer, deposition time, and the emissivity of the layer to electromagnetic radiation of 810 nm [[is]] are shown in Table 2.

TABLE 2

Substrate	Approximate Thickness (Å)	Emissivity	Deposition Time (Sec)
10	800	0.91	17
11	900	0.95	19
12	1000	0.98	21
13	1100	0.99	24
14	1200	0.99	26
15	1300	0.97	28
16	850	0.94	17
17	1200	0.98	25